

an upper cylinder edge of the storage electrode being rounded and having a larger thickness than a thickness in the rest portion.

Claim A

2. (Amended) A semiconductor device according to claim 1, wherein the storage electrode has a thickness gradually thickened toward to the upper cylinder edge.

3. (Amended) A semiconductor device according to claim 1, wherein a side surface of the storage electrode is tilted and a peripheral length of a cylinder is gradually increased toward to the upper cylinder edge.

4. (Amended) A semiconductor device according to claim 2, wherein a side surface of the storage electrode is tilted and a peripheral length of a cylinder is gradually increased toward to the upper cylinder edge.

Claim B17

7. (Amended) A semiconductor device according to claim 1, wherein an inner surface of the storage electrode at a border portion between a side surface and a bottom surface is rounded.

8. (Amended) A semiconductor device according to claim 2, wherein

an inner surface of the storage electrode at a border portion between a side surface and a bottom surface is rounded.

Cmt
A2

9. (Amended) A semiconductor device comprising:

a capacitor formed above a semiconductor substrate and including

a cylindrical-shaped storage electrode,

a capacitor dielectric film formed on the storage electrode, and

a plate electrode formed on the capacitor dielectric film,

the storage electrode being formed of a metal film and having a larger thickness at an upper cylinder edge than a thickness in a rest portion.

10. (Amended) A semiconductor device according to claim 9, wherein

the storage electrode has a thickness gradually thickened toward to the upper cylinder edge.

11. (Amended) A semiconductor device comprising:

a capacitor formed above a semiconductor substrate and including

a cylindrical-shaped storage electrode,

a capacitor dielectric film formed on the storage electrode, and

a plate electrode formed on the capacitor dielectric film,

cmt a2

the storage electrode being formed of a metal film and an upper cylinder edge of the storage electrode being rounded.

12. (Amended) A semiconductor device according to claim 11, wherein

the storage electrode has a thickness gradually thickened toward to the upper cylinder edge.